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DIODES, POWER RECTIFIER, SCHOTTKY BARRIER

BASED ON TYPE STPS1045

ESCC Detail Specification No. 5106/017

April 2007	Issue 2	April 2007	
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DCR No.	CHANGE DESCRIPTION
270	Specification up issued to incorporate editorial and technical changes per DCR.







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1. **GENERAL**

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 5000
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 <u>The ESCC Component Number</u>

The ESCC Component Number shall be constituted as follows:

Example: 510601701

• Detail Specification Reference: 5106017

Component Type Variant Number: 01 (as required)

1.4.2 <u>Component Type Variants</u>

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Description	Terminal Material and Finish	Weight max g
01	STPS1045	SMD.5	Single diode	Q14	2
02	STPS1045	SMD.5	Dual diode, common cathode	Q14	2

The terminal material and finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Forward Surge Current (per Diode)	I _{FSM}	200	Α	Note 1





Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Repetitive Peak Reverse Voltage	V _{RRM}	45	V	Note 2
Repetitive Peak Reverse Current	I _{RRM}	1	Α	Note 3
Average Output Rectified Current Variants 01 and 02 (per Diode) Variant 02 (per Device)	lo	10 20	A	50% Duty Cycle Notes 4, 7
RMS Forward Current (per Diode)	I _{F(rms)}	15	Α	
Operating Temperature Range (Case Temperature)	T _{op}	-65 to +175	°C	
Junction Temperature	Tj	+175	°C	
Storage Temperature Range	T _{stg}	-65 to +175	°C	
Soldering Temperature	T _{sol}	+245	°C	Note 5
Critical Rate of Rise of Reverse Voltage	dV/dt	10000	V/μs	
Thermal Resistance, Junction to Case Variant 01 and 02 (per Diode) Variant 02 (per Device)	R _{th(j-c)}	2.8 1.6	°C/W	Notes 6, 7

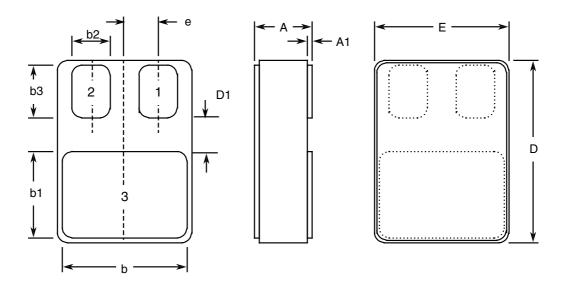
NOTES:

- 1. Sinusoidal pulse of 10ms duration.
- 2. Pulsed, duration 5ms, f = 50Hz.
- 3. Pulsed, duration $2\mu s$, f = 1kHz.
- 4. For Variants 01 and 02 per Diode at $T_{case} > +154^{\circ}C$, or Variant 02 per Device at $T_{case} > +151^{\circ}C$, derate linearly to 0A at $+175^{\circ}C$.
- 5. Duration 5 seconds maximum and the same package shall not be resoldered until 3 minutes have elapsed.
- 6. Package mounted on infinite heatsink.
- 7. For Variant 02 the "per Device" ratings apply only when both anode terminals are tied together.



1.6 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

1.6.1 <u>Surface Mount Package (SMD.5) - 3 Terminal</u>



Symbols	Dimensio	Notes	
Symbols	Min	Max	Notes
А	2.84	3.15	
A1	0.25	0.51	
b	7.13	7.39	
b1	5.58	5.84	
b2	2.28	2.54	2
b3	2.92	3.18	2
D	10.03	10.28	
D1	0.76	-	2
Е	7.39	7.64	
е	1.91 BSC		2

NOTES:

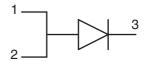
- 1. The terminal identification is specified by the component's geometry. See Functional Diagram for the terminal connections.
- 2. 2 places.



1.7 <u>FUNCTIONAL DIAGRAM</u>

Variant 01

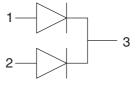
Terminal 1 and 2: Anode Terminal 3: Cathode



Variant 02

Terminal 1: Anode a Terminal 2: Anode b

Terminal 3: Common Cathode



NOTES:

1. The lid is not connected to any terminal.

1.8 MATERIALS AND FINISHES

Materials and finishes shall be as follows:

- a) Case
 - The case shall be hermetically sealed and have a ceramic body with a Kovar lid.
- b) Terminals

As specified in Component Type Variants.

2. REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

2.1.1.1 Deviation from Screening Tests - Chart F3

(a) High Temperature Reverse Bias Burn-in and the subsequent Final Measurements for HTRB shall be omitted.

2.1.1.2 Deviations from Qualification and Periodic Tests - Chart F4

(a) Constant Acceleration is not applicable.



(b) Terminal Strength is not applicable.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) The ESCC qualified components symbol (for ESCC qualified components only).
- (b) The ESCC Component Number.
- (c) Traceability information.

2.3 <u>ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES</u>

Electrical measurements shall be performed at room, high and low temperatures. Consolidated notes are given after the tables.

2.3.1 Room Temperature Electrical Measurements

The measurements shall be performed at T_{amb} =+22 ±3°C.

Characteristics	Symbols	MIL-STD-750	Test Conditions	Limits		Units
		Test Method	Note 1	Min	Max	
Reverse Current	I _R	4016	DC Method V _R = 45V	-	100	μΑ
Forward Voltage	V _{F1}	4011	Pulse Method I _F =3A, Note 2	-	620	mV
	V _{F2}	4011	Pulse Method I _F =10A, Note 2	-	750	mV
	V _{F3}	4011	Pulse Method I _F =20A, Note 2	-	880	mV
Capacitance	С	4001	V _R = 5V f = 1MHz	-	500	pF
Thermal Impedance, Junction to Case	Z _{th(j-c)}	3101	I_H = 15 to 40A t_H = 50ms I_M = 50mA t_{md} = 100 μ s Note 3		ate ΔV _F , lote 4)	°C/W

2.3.2 <u>High and Low Temperatures Electrical Measurements</u>

Characteristics	Symbols	MIL-STD-750	Test Conditions	Lin	nits	Units
		Test Method	Notes 1 and 5	Min	Max	
Reverse Current	I _R	4016	T _{case} =+125 (+0 -5)°C DC Method V _R = 45V	-	15	mA



Characteristics	Symbols	MIL-STD-750 Test Conditions				nits	Units
		Test Method	st Method Notes 1 and 5		Max		
Forward Voltage	V _{F1}	4011	T _{case} =+125 (+0 -5) ^o C Pulse Method I _F =3A, Note 3	•	570	mV	
	V _{F2}	4011	T _{case} =+125 (+0 -5)°C Pulse Method I _F =10A, Note 3	-	700	mV	
			T _{case} =-55(+5 -0)°C Pulse Method I _F =10A, Note 3	-	850		
	V _{F3}	4011	T _{case} =+125 (+0 -5)°C Pulse Method I _F =20A, Note 3	-	800	mV	

2.3.3 <u>Notes to Electrical Measurement Tables</u>

- 1. Measurement per each Diode.
- 2. Pulse Width ≤ 300μs, Duty Cycle ≤ 2%
- 3. Performed only during Screening Tests Parameter Drift Values (Initial Measurements), go-no-go.
- 4. The limits for ΔV_F shall be defined by the Manufacturer on every lot in accordance with MIL-STD-750 Method 3101 and shall guarantee the $R_{th(i-c)}$ limits specified in Maximum Ratings.
- 5. Read and record measurements shall be performed on a sample of 5 components with 0 failures. Alternatively a 100% inspection may be performed.

2.4 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at T_{amb} =+22 ±3°C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols Limits		Limits		Units
		Drift	Abso	olute	
		Value Δ	Min	Max	
Reverse Current	I _R	±25 or (1) ±100%	-	100	μА
Forward Voltage	V _{F1}	±50	-	620	mV
	V _{F3}	±50	-	880	mV

NOTES:

1. Whichever is the greater referred to the initial value.



2.5 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at T_{amb} =+22 $\pm 3^{o}$ C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements .

The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits		Units
		Min	Max	
Reverse Current	I _R	-	100	μΑ
Forward Voltage	V _{F1}	-	620	mV
	V _{F2}	-	750	mV
	V _{F3}	-	880	mV

2.6 POWER BURN-IN CONDITIONS

Characteristics	Symbols	Test Conditions	Units
Case Temperature	T _{case}	+125	°C
Reverse Voltage	V _R	36	V

2.7 <u>OPERATING LIFE CONDITIONS</u>

The conditions shall be as specified for Power Burn-in.



APPENDIX 'A'

AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
Deviations from Production Control- Chart F2	Special In-process Control Internal Visual Inspection. Wedge bonds equal to 1.1 wire diameters are acceptable for bonding with a V-Groove tool.